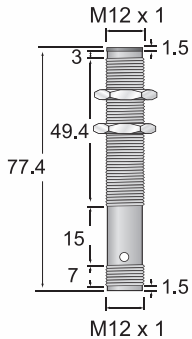
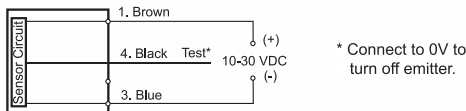
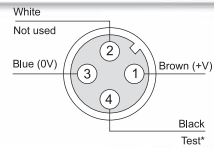
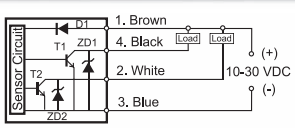
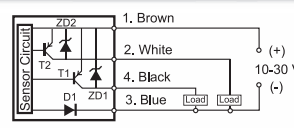


M12 SERIES

M12 Series			
Image	Series Description	Modes	Range
	Cylindrical Photoelectric Sensor - Standard 12mm Housing - Pre-wired or Quick Disconnect - Self-contained Amplifier	Through Beam	5.2m
		Retroreflective	1m
		Diffuse	200mm
	Through-beam	Diffuse	Retroreflective (Polarized)
Operating Range	5.2m (17.06 ft.)	0.2m (0.66 ft.)	1m (3.28 ft.)
Light Emission	880nm Infrared LED		660nm Red LED
Part Numbers			
Emitter	M12B-T5200D-EX9Q4LE		
NPN - Light/Dark	M12B-T5200N-CX9Q4UE	M12B-D0200N-CX9Q4UE	M12B-L1000N-CX6Q4UE-PF
PNP - Light/Dark	M12B-T5200P-CX9Q4UE	M12B-D0200P-CX9Q4UE	M12B-L1000P-CX6Q4UE-PF
Technical Data			
Power Supply	10...30 VDC		
Current Consumption	30mA max.		
Indicator LEDs	Red LED (output activated)		
Voltage Drop	2.5 V or less		
Current Load Max	200mA		
Response Time	1.5ms		
Connection	M12 - Recommended Mating Cable: part # R-FS4TZ-V075 (straight), R-FA4TZ-V075 (right-angle)		
Electrical Protection	Short-circuit, Reverse Polarity and Overload Current Protection		
Mechanical Protection	IP67 (IEC)		
Housing Material	Metal: Nickel-plated Brass; Plastic: PBT		
Environment	-25°C to +55°C (-13°F to 131°F) ; 35-85% RH		
Storage Temp.	-25°C to + 70°C (-13°F to +158°F)		
Reference Standard	IEC 60947-5-2		
Dimensions	Connections		
	Emitter		Emitter
			
	NPN	PNP	NPN / PNP
	 D1: Reverse polarity protection diode ZD1, ZD2: Surge absorption zener diode T1, T2: NPN output transistor	 D1: Reverse polarity protection diode ZD1, ZD2: Surge absorption zener diode T1, T2: PNP output transistor	